# MBL1S THRU MBL10S

# **Bridge Rectifier**



#### ■特征 Features

• I<sub>o</sub> 0.8A

• V<sub>RRM</sub> 100V~1000V

• 玻璃钝化芯片

Glass passivated chip

耐正向浪涌电流能力高
High surge forward current capability

### ■用途 Applications

●作一般电源单相桥式整流用
General purpose 1 phase Bridge rectifier applications

# ■极限值(绝对最大额定值)

# **Limiting Values (Absolute Maximum Rating)**

■外形尺寸 Outline Dimensions and Mark
MBLS
.008(0.20) .008(0.20) .157(4.50) .288(6.50) .142(3.60) .283(7.20) .097(2.20) .193(5.00) .177(4.50)
.033(0.84) .022(0.56) Dimensions in inches and (millimeters)

参数名称	符号	单位	条件		MBL					
Item	Symbol	Unit	•	Conditions	1S 2S	48	6S	88	10S	
反向重复峰值电压 Repetitive Peak Reverse Voltage	$V_{RRM}$	<b>V</b>			100	200	400	600	800	1000
平均整流输出电流	l <sub>a</sub>	Α	60Hz正弦波, 电阻负载, Ta=25℃	安装在氧化铝基板上 On alumina substrate	0.8					
Average Rectified Output Io Current	I <sub>O</sub>	A	60Hz sine wave, R-load, Ta=25°C	安装在玻璃-环氧基板上 On glass-epoxi substrate	0.5					
正向(不重复)浪涌电流 Surge(Non- repetitive)Forward Current	I <sub>FSM</sub>	Α	60Hz正弦波,一个周期,Tj=25℃ 60Hz sine wave, 1 cycle, Tj=25℃			35				
正向浪涌电流的平方对电流 浪涌持续时间的积分值 Current Squared Time	l <sup>2</sup> t	A <sup>2</sup> S	1ms≤t<8.3ms Tj=25℃,单个二极管 1ms≤t<8.3ms Tj=25℃,Rating of per diode			5.1				
存储温度 Storage Temperature	$T_{stg}$	$^{\circ}$					-55 ~	+150		
结温 Junction Temperature	Tj	$^{\circ}$	-55 ~+150							

# ■电特性 (Ta=25℃ 除非另有规定)

**Electrical Characteristics** (T<sub>a</sub>=25℃ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	最大值 Max
正向峰值电压 Peak Forward Voltage	V <sub>FM</sub>	V	I <sub>FM</sub> =0.4A, 脉冲测试,单个二极管的额定值 I <sub>FM</sub> =0.4A, Pulse measurement, Rating of per diode	1.0
反向峰值电流 Peak Reverse Current	I <sub>RRM</sub>	Α	V <sub>RM</sub> =V <sub>RRM</sub> ,脉冲测试,单个二极管的额定值 V <sub>RM</sub> =V <sub>RRM</sub> , Pulse measurement, Rating of per diode	10
热阻 Thermal Resistance	R θ J-A	℃W	结和环境之间,安装在氧化铝基板上 Between junction and ambient, On alumina substrate	76
	IX 0 J-A		结和环境之间,安装在玻璃-环氧基板上 Between junction and ambient, On glass-epoxi substrate	134
	R θ J-L		结和引线之间 Between junction and lead	20

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### ■特性曲线(典型) Characteristics(Typical)

图1: lo-Ta曲线 FIG1:lo-Ta Curve € 1.2 (2) 1mm $\times 1$ mm 1mm $\times$  1mm 焊接区soldering land 35um 20um 导体箔conductor layer 1.0 基板厚度substrate thickness 0.64mm ②在氧化铝基板上 0.8 on alumina substrate 正弦波, 电阻负载, 0.6 用散热片 sine wave R-load with heatsink 0.4 ①在玻璃-环氧基板上 0.2 on glass-epoxi substrate 0 0 40 80 120 160 Ta(℃)

图2: 耐正向浪涌电流曲线 FIG2:Surge Forward Current Capadility 正弦波 35 sine wave 30 8.3ms 8.3ms 1 cycle 25 不重复 non-repetitive 20 Tj=25 ℃ 15 10 5 0 2 5 20 50 10 100 **Number of Cycles** 

